

**IN THE CLAIMS**

Please amend the claims as follows:

1-2 (Cancelled)

a potential of the first bit line is higher than a threshold of the P-channel MOS transistor.

3. (Currently amended) A semiconductor device, comprising:

a differential sense amplifier connected to a bit line; and

a data transfer circuit including a column selection switch for turning ON/OFF the  
connection between a data line and the bit line,

wherein the column selection switch includes a read column selection switch and a write  
column selection switch, and

wherein the bit line is connected to the same data line via the read column selection switch  
and the write column selection switch, separately.

4. (Original) The semiconductor device of claim 3, wherein an on-state resistance of the  
read column selection switch is higher than that of the write column selection switch.

5. (Original) The semiconductor device of claim 3, wherein the read column selection  
switch and the write column selection switch are connected to the data line via a common impurity  
diffusion layer.

6-8 (Cancelled)

9. (New) A semiconductor device, comprising:

a first differential sense amplifier connected to a first bit line;

a second differential sense amplifier connected to a second bit line and being adjacent to the  
first differential sense amplifier; and

a data transfer circuit including a first column selection switch for turning ON/OFF the connection between a data line and the first bit line, and a second column selection switch for turning ON/OFF the connection between the data line and the second bit line,

wherein the first column selection switch includes a first read column selection switch and a first write column selection switch,

the second column selection switch includes a second read column selection switch and a second write column selection switch,

the first bit line is connected to the same data line via the first read column selection switch and the first write column selection switch, separately,

the second bit line is connected to the same data line via the second read column selection switch and the second write column selection switch, separately, and

all connection portions between the data line and each of the first read column selection switch, the first write column selection switch, the second read column selection switch, and the second write column selection switch comprise a common impurity diffusion layer.